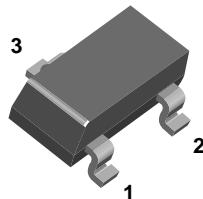
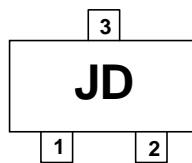




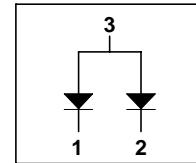
## BAW74



SOT-23



Connection Diagram



### Small Signal Diode

#### Absolute Maximum Ratings\*

 $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Value	Units
$V_{RRM}$	Maximum Repetitive Reverse Voltage	50	V
$I_{F(AV)}$	Average Rectified Forward Current	200	mA
$I_{FSM}$	Non-repetitive Peak Forward Surge Current Pulse Width = 1.0 second Pulse Width = 1.0 microsecond	1.0 2.0	A A
$T_{stg}$	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature	150	$^\circ\text{C}$

\* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

## NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

#### Thermal Characteristics

Symbol	Parameter	Value	Units
$P_D$	Power Dissipation	350	mW
$R_{JJA}$	Thermal Resistance, Junction to Ambient	357	$^\circ\text{C}/\text{W}$

#### Electrical Characteristics

 $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
$V_R$	Breakdown Voltage	$I_R = 100 \mu\text{A}$	50		V
$V_F^*$	Forward Voltage	$I_F = 100 \text{ mA}$		1.0	V
$I_R^*$	Reverse Current	$V_R = 50 \text{ V}, T_A = 150^\circ\text{C}$		100	$\mu\text{A}$
$C_T$	Total Capacitance	$V_R = 0, f = 1.0 \text{ MHz}$		2.0	pF
$t_{rr}$	Reverse Recovery Time	$I_F = I_R = 10 \text{ mA}, I_{RR} = 1.0 \text{ mA}, R_L = 100 \Omega$		4.0	ns

\* Pulse test : Pulse width=300us, Duty Cycle=2%